# MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PIFD

S9018

Product specification





#### TRANSISTOR (NPN)

#### **FEATURES**

- AM/FM Amplifier, Local Oscillator of FM/VHF Tuner
- High Current Gain Bandwidth Product

#### **Reference News**

PACKAGE OUTLINE		MARKING		
1 2	1. BASE 2. EMITTER 3.COLLECTOR	J8		
SOT-23				

# MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>СВО</sub>	Collector-Base Voltage	30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	15	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
lc	Collector Current -Continuous	50	mA
Pc	Collector Power Dissipation	200	mW
ReJA	Thermal Resistance from Junction to Ambient	625	°C/W
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55-150	${\mathbb C}$

# **ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)**

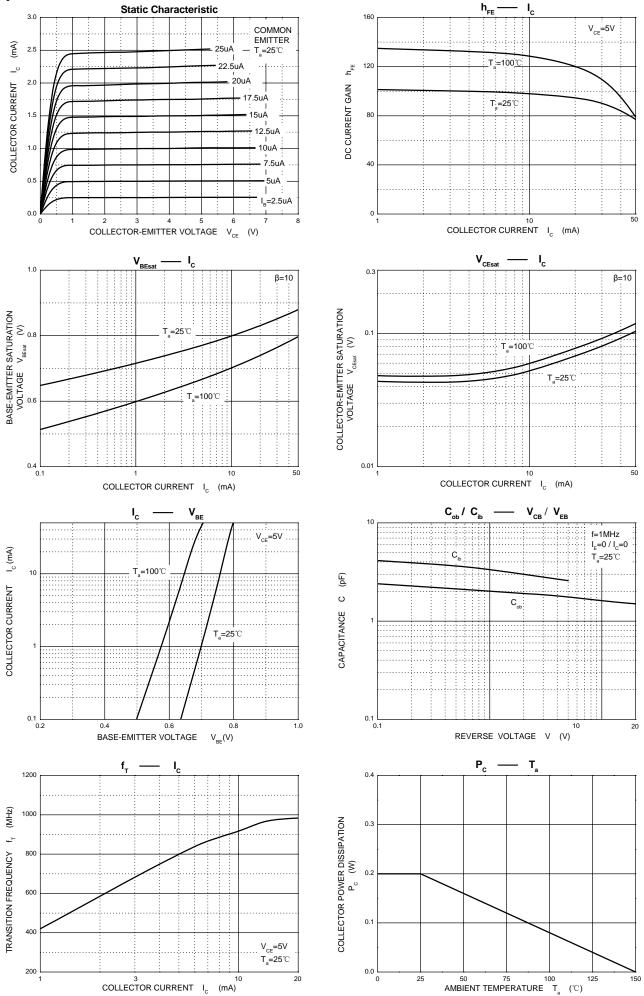
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)</sub> CBO	I <sub>C</sub> = 100μA, I <sub>E</sub> =0	30			V
Collector-emitter breakdown voltage	V <sub>(BR)</sub> CEO	Ic= 1mA, I <sub>B</sub> =0	15			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	l <sub>E</sub> =100μA, I <sub>C</sub> =0	5			V
Collector cut-off current	Ісво	V <sub>CB</sub> =12V, I <sub>E</sub> =0			0.05	μA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =12V, I <sub>B</sub> =0			0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 3V, I <sub>C</sub> =0			0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> = 1mA	70		200	
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	lc=10mA, I <sub>B</sub> = 1mA			0.5	V
Base-emitter saturation voltage	V <sub>BE</sub> (sat)	I <sub>C</sub> =10mA, I <sub>B</sub> = 1mA			1.4	V
Transition frequency	f⊤	V <sub>CE</sub> =5V, I <sub>C</sub> = 5mA f=400MHz		800		MHz

# **CLASSIFICATION OF hFE(1)**

Rank	L	Н
Range	70-100	100-200

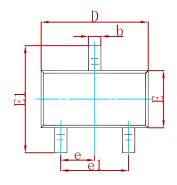


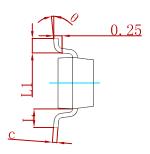
## **Typical Characteristics**

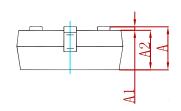




## PACKAGE MECHANICAL DATA

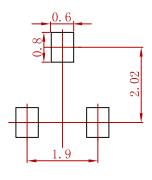






Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Эунюог	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.03	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022	2 REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.

## **REEL SPECIFICATION**

P/N	PKG	QTY
S9018	SOT-23	3000



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